

isc Silicon NPN Power Transistor

2SD350

DESCRIPTION

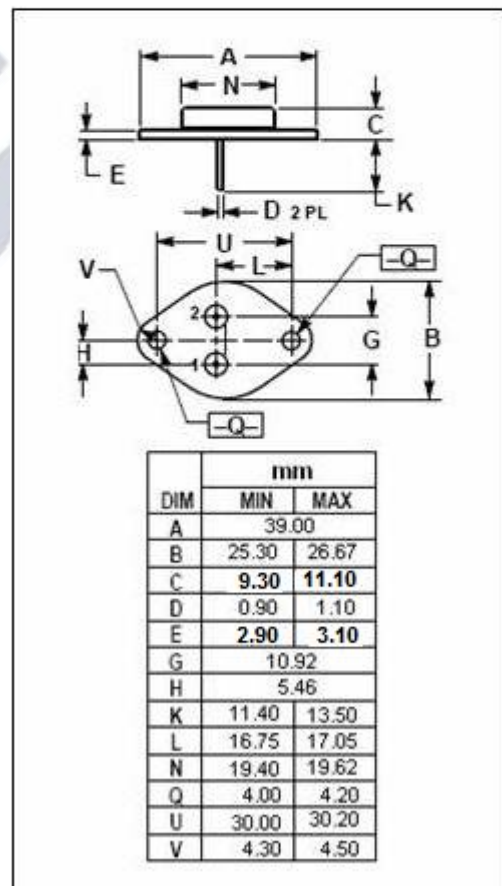
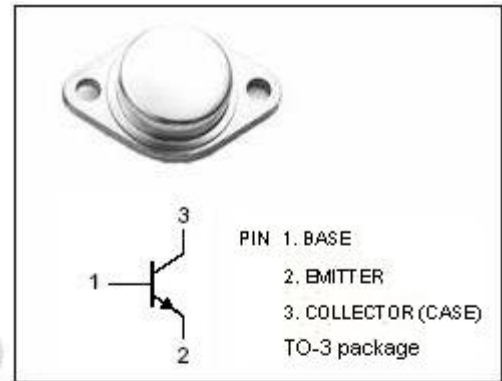
- Collector-Emitter Sustaining Voltage-
: $V_{CEO(SUS)} = 700V$ (Min)
- High Switching Speed
- Wide Area of Safe Operation
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for use in horizontal deflection circuits of color TV receivers and switching applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	1500	V
V_{CEO}	Collector-Emitter Voltage	700	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current- Continuous	5	A
I_{CM}	Collector Current-Peak	8	A
P_C	Collector Power Dissipation @ $T_C=90^\circ C$	35	W
T_J	Junction Temperature	130	$^\circ C$
T_{stg}	Storage Temperature Range	-65~130	$^\circ C$



isc Silicon NPN Power Transistor**2SD350****ELECTRICAL CHARACTERISTICS****T_c=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 10mA; R _{BE} = ∞	700			V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = 1mA; I _E = 0	1500			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = 1mA; I _C = 0	6			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 4.5A; I _B = 2.0A			1.0	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 4.5A; I _B = 2.0A			1.3	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 1500V; I _E = 0			1	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 6V; I _C = 0			100	μ A
h _{FE-1}	DC Current Gain	I _C = 0.1A; V _{CE} = 5V	6		30	
h _{FE-2}	DC Current Gain	I _C = 4A; V _{CE} = 10V	3			
f _T	Current-Gain—Bandwidth Product	I _C = 0.1A; V _{CE} = 5V		6		MHz
t _f	Fall Time	I _C = 4.5A; I _B = 2.0A			1.0	μ s